Baolai Liang

List of Publications by Year
in descending order

141 papers	2,764 citations	201674 27 h-index	223800 46 g-index
142 all docs	142 docs citations	142 times ranked	2792 citing authors

#	Article	IF	Citations
1	Nanoholes fabricated by self-assembled gallium nanodrill on GaAs(100). Applied Physics Letters, 2007, 90, 113120.	3.3	209
2	A vertically layered MoS₂/Si heterojunction for an ultrahigh and ultrafast photoresponse photodetector. Journal of Materials Chemistry C, 2018, 6, 3233-3239.	5.5	132
3	Bottom-up Photonic Crystal Lasers. Nano Letters, 2011, 11, 5387-5390.	9.1	112
4	Surface Plasmon-Enhanced Nanopillar Photodetectors. Nano Letters, 2011, 11, 5279-5283.	9.1	108
5	Ultrahigh, Ultrafast, and Selfâ€Powered Visibleâ€Nearâ€Infrared Optical Positionâ€Sensitive Detector Based on a CVDâ€Prepared Vertically Standing Fewâ€Layer MoS₂/Si Heterojunction. Advanced Science, 2018, 5, 1700502.	11.2	87
6	Self-Catalyzed Epitaxial Growth of Vertical Indium Phosphide Nanowires on Silicon. Nano Letters, 2009, 9, 2223-2228.	9.1	70
7	Low density InAs quantum dots grown on GaAs nanoholes. Applied Physics Letters, 2006, 89, 043113.	3.3	68
8	CdS/Sb₂S₃ heterojunction thin film solar cells with a thermally evaporated absorber. Journal of Materials Chemistry C, 2017, 5, 9421-9428.	5.5	68
9	Extremely low excess noise and high sensitivity AlAs0.56Sb0.44 avalanche photodiodes. Nature Photonics, 2019, 13, 683-686.	31.4	62
10	InGaAs heterostructure formation in catalyst-free GaAs nanopillars by selective-area metal-organic vapor phase epitaxy. Applied Physics Letters, 2010, 97, .	3.3	59
11	Piezophototronic Effect Enhanced Photoresponse of the Flexible Cu(In,Ga)Se₂ (CIGS) Heterojunction Photodetectors. Advanced Functional Materials, 2018, 28, 1707311.	14.9	58
12	General heterostructure strategy of photothermal materials for scalable solar-heating hydrogen production without the consumption of artificial energy. Nature Communications, 2022, 13, 776.	12.8	56
13	Mechanism of the trivalent lanthanidesâ€™ persistent luminescence in wide bandgap materials. Light: Science and Applications, 2022, 11, 51.	16.6	52
14	Structural Analysis of Highly Relaxed GaSb Grown on GaAs Substrates with Periodic Interfacial Array of 90Â° Misfit Dislocations. Nanoscale Research Letters, 2009, 4, 1458-62.	5.7	50
15	Self-Organization of InAs Quantum-Dot Clusters Directed by Droplet Homoepitaxy. Small, 2007, 3, 235-238.	10.0	45
16	GaSb thermophotovoltaic cells grown on GaAs by molecular beam epitaxy using interfacial misfit arrays. Applied Physics Letters, 2015, 106, .	3.3	41
17	Review Article: Molecular beam epitaxy of lattice-matched InAlAs and InGaAs layers on InP (111)A, (111)B, and (110). Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2017, 35, .	1.2	41
18	Localized formation of InAs quantum dots on shallow-patterned GaAs(100). Applied Physics Letters, 2006, 88, 233102.	3.3	40

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19	GaSb/GaAs type-II quantum dots grown by droplet epitaxy. Nanotechnology, 2009, 20, 455604.	2.6	39
20	Origin of nanohole formation by etching based on droplet epitaxy. Nanoscale, 2014, 6, 2675.	5.6	37
21	Development of continuum states in photoluminescence of self-assembled InGaAsâˆ•GaAs quantum dots. Journal of Applied Physics, 2007, 101, 014301.	2.5	34
22	Tuning Quantum Dot Luminescence Below the Bulk Band Gap Using Tensile Strain. ACS Nano, 2013, 7, 5017-5023.	14.6	34
23	Characterization of GaSb/GaAs interfacial misfit arrays using x-ray diffraction. Applied Physics Letters, 2011, 99, .	3.3	33
24	Strain-driven growth of GaAs(111) quantum dots with low fine structure splitting. Applied Physics Letters, 2014, 105, .	3.3	33
25	Band Alignment Tailoring of InAs_{1âˆ’<i>x</i>}Sb_{<i>x</i>}/GaAs Quantum Dots: Control of Type I to Type II Transition. Nano Letters, 2010, 10, 3052-3056.	9.1	31
26	Direct Spectroscopic Evidence for the Formation of One-Dimensional Wetting Wires During the Growth of InGaAs/GaAs Quantum Dot Chains. Nano Letters, 2006, 6, 1847-1851.	9.1	30
27	Coexistence of type-I and type-II band alignments in antimony-incorporated InAsSb quantum dot nanostructures. Applied Physics Letters, 2012, 100, .	3.3	30
28	Structural and optical properties of InAs/AlAsSb quantum dots with GaAs(Sb) cladding layers. Applied Physics Letters, 2012, 100, .	3.3	28
29	One-step hydrothermal synthesis of NiCo2S4 loaded on electrospun carbon nanofibers as an efficient counter electrode for dye-sensitized solar cells. Solar Energy, 2020, 202, 358-364.	6.1	27
30	Lateral photovoltaic effect observed in doping-modulated GaAs/Al_03Ga_07As. Optics Express, 2017, 25, A166.	3.4	25
31	Excitonic transfer in coupled InGaAsâˆ•GaAs quantum well to InAs quantum dots. Applied Physics Letters, 2006, 89, 151914.	3.3	24
32	Selective growth of InGaAs/GaAs quantum dot chains on pre-patterned GaAs(100). Nanotechnology, 2006, 17, 2275-2278.	2.6	24
33	Size and density control of InAs quantum dot ensembles on self-assembled nanostructured templates. Semiconductor Science and Technology, 2006, 21, 1547-1551.	2.0	24
34	Time-resolved photoluminescence of type-II Ga(As)Sb/GaAs quantum dots embedded in an InGaAs quantum well. Nanotechnology, 2008, 19, 295704.	2.6	24
35	Synthesis of mesoporous Fe₃Si aerogel as a photo-thermal material for highly efficient and stable corrosive-water evaporation. Journal of Materials Chemistry A, 2018, 6, 23263-23269.	10.3	23
36	InGaAs quantum dots grown on B-type high index GaAs substrates: surface morphologies and optical properties. Nanotechnology, 2006, 17, 2736-2740.	2.6	22

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37	Correlation between surface and buried InAs quantum dots. Applied Physics Letters, 2006, 89, 043125.	3.3	22
38	Photoluminescence Study of the Interface Fluctuation Effect for InGaAs/InAlAs/InP Single Quantum Well with Different Thickness. Nanoscale Research Letters, 2017, 12, 229.	5.7	22
39	Demonstration of large ionization coefficient ratio in AlAs0.56Sb0.44 lattice matched to InP. Scientific Reports, 2018, 8, 9107.	3.3	22
40	Influence of GaAs Substrate Orientation on InAs Quantum Dots: Surface Morphology, Critical Thickness, and Optical Properties. Nanoscale Research Letters, 2007, 2, .	5.7	21
41	Photoconductive gain in patterned nanopillar photodetector arrays. Applied Physics Letters, 2010, 97, .	3.3	21
42	Photoluminescence of surface InAs quantum dot stacking on multilayer buried quantum dots. Applied Physics Letters, 2006, 89, 243124.	3.3	20
43	Optical properties of patterned InAs quantum dot ensembles grown on GaAs nanopyramids. Applied Physics Letters, 2007, 91, .	3.3	19
44	Self-assembly of (111)-oriented tensile-strained quantum dots by molecular beam epitaxy. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2018, 36, .	1.2	19
45	Anomalous Stranski-Krastanov growth of (111)-oriented quantum dots with tunable wetting layer thickness. Scientific Reports, 2019, 9, 18179.	3.3	19
46	Extracting transport parameters in GaAs nanopillars grown by selective-area epitaxy. Nanotechnology, 2012, 23, 105701.	2.6	18
47	Hybrid type-I InAs/GaAs and type-II GaSb/GaAs quantum dot structure with enhanced photoluminescence. Applied Physics Letters, 2015, 106, .	3.3	18
48	Lengthening of the photoluminescence decay time of InAs quantum dots coupled to InGaAsâˆ•GaAs quantum well. Journal of Applied Physics, 2006, 100, 054313.	2.5	17
49	Near-field optical spectroscopy ofGaAsâˆ•AlyGa1âˆ’yAsquantum dot pairs grown by high-temperature droplet epitaxy. Physical Review B, 2008, 77, .	3.2	17
50	Improved quantum dot stacking for intermediate band solar cells using strain compensation. Nanotechnology, 2014, 25, 445402.	2.6	17
51	Comparative study of photoluminescence from In_{0.3}Ga_{0.7}As/GaAs surface and buried quantum dots. Nanotechnology, 2016, 27, 465701.	2.6	17
52	Interplay Effect of Temperature and Excitation Intensity on the Photoluminescence Characteristics of InGaAs/GaAs Surface Quantum Dots. Nanoscale Research Letters, 2018, 13, 387.	5.7	17
53	The split-up of G band and 2D band in temperature-dependent Raman spectra of suspended graphene. Optics and Laser Technology, 2021, 139, 106960.	4.6	17
54	Tuning the optical performance of surface quantum dots in InGaAs/GaAs hybrid structures. Optics Express, 2007, 15, 8157.	3.4	16

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55	Improved photoluminescence efficiency of patterned quantum dots incorporating a dots-in-the-well structure. Nanotechnology, 2008, 19, 435710.	2.6	16
56	Effects of different Cs distribution in the film on the performance of CIGS thin film solar cells. Solar Energy Materials and Solar Cells, 2021, 222, 110917.	6.2	16
57	Site-controlled formation of InGaAs quantum nanostructures-Tailoring the dimensionality and the quantum confinement. Nano Research, 2013, 6, 235-242.	10.4	14
58	The transverse thermoelectric effect in <i>a</i>-axis inclined oriented SnSe thin films. Journal of Materials Chemistry C, 2018, 6, 12858-12863.	5.5	14
59	Layer-number dependent reflection spectra of MoS₂ flakes on SiO₂/Si substrate. Optical Materials Express, 2018, 8, 3082.	3.0	14
60	Coke and sintering resistant nickel atomically doped with ceria nanosheets for highly efficient solar driven hydrogen production from bioethanol. Green Chemistry, 2022, 24, 2044-2050.	9.0	14
61	Composite axial/core-shell nanopillar light-emitting diodes at 1.3â€‰<i>Î¼</i>m. Applied Physics Letters, 2012, 101, 053111.	3.3	13
62	Electronic Coupling in Nanoscale InAs/GaAs Quantum Dot Pairs Separated by a Thin Ga(Al)As Spacer. Nanoscale Research Letters, 2015, 10, 973.	5.7	13
63	A Precursor Stacking Strategy to Boost Open-Circuit Voltage of Cu₂ZnSnS₄Thin-Film Solar Cells. IEEE Journal of Photovoltaics, 2018, 8, 856-863.	2.5	13
64	Full-color photon-counting single-pixel imaging. Optics Letters, 2021, 46, 4900.	3.3	13
65	Effects of GaAs(Sb) cladding layers on InAs/AlAsSb quantum dots. Applied Physics Letters, 2013, 102, .	3.3	12
66	Tensile GaAs(111) quantum dashes with tunable luminescence below the bulk bandgap. Applied Physics Letters, 2014, 105, .	3.3	12
67	Temperature Dependence of Raman-Active In-Plane E2g Phonons in Layered Graphene and h-BN Flakes. Nanoscale Research Letters, 2018, 13, 25.	5.7	12
68	Complex-amplitude single-pixel imaging using coherent structured illumination. Optics Express, 2021, 29, 41827.	3.4	12
69	Lateral photovoltaic effect based on novel materials and external modulations. Journal Physics D: Applied Physics, 2021, 54, 153003.	2.8	11
70	Temperature Dependence of the Impact Ionization Coefficients in AlAsSb Lattice Matched to InP. IEEE Journal of Selected Topics in Quantum Electronics, 2022, 28, 1-8.	2.9	11
71	Four-wave mixing and edge-enhanced optical correlation in a Ce:KNSBN crystal. Optics Letters, 2000, 25, 1086.	3.3	10
72	Carrier dynamics in hybrid nanostructure with electronic coupling from an InGaAs quantum well to InAs quantum dots. Journal of Luminescence, 2018, 202, 20-26.	3.1	10

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73	Correlation between photoluminescence and morphology for single layer self-assembled InGaAs/GaAs quantum dots. Optics Express, 2018, 26, 23107.	3.4	10
74	Impact Ionization Coefficients of Digital Alloy and Random Alloy Al_{0.85}Ga_{0.15}As_{0.56}Sb_{0.44} in a Wide Electric Field Range. Journal of Lightwave Technology, 2022, 40, 4758-4764.	4.6	10
75	Annealing effect on GaAs droplet templates in formation of self-assembled InAs quantum dots. Applied Physics Letters, 2006, 89, 213103.	3.3	9
76	High-density InAs/GaAs1âˆ’<i>x</i>Sb<i>x</i> quantum-dot structures grown by molecular beam epitaxy for use in intermediate band solar cells. Journal of Applied Physics, 2016, 119, .	2.5	9
77	Absorption dynamics of type-II GaSb/GaAs quantum dots. Optical Materials Express, 2017, 7, 1424.	3.0	9
78	Localized state effect and exciton dynamics for monolayer WS₂. Optics Express, 2021, 29, 5856.	3.4	9
79	Temperature Dependence of G and Dâ€™ Phonons in Monolayer to Few-Layer Graphene with Vacancies. Nanoscale Research Letters, 2020, 15, 189.	5.7	9
80	InAs Quantum Dots on Nanopatterned GaAs (001) Surface: The Growth, Optical Properties, and Device Implementation. Journal of Nanoscience and Nanotechnology, 2010, 10, 1537-1550.	0.9	8
81	Controlled Formation and Dynamic Wulff Simulation of Equilibrium Crystal Shapes of GaAs Pyramidal Structures on Nanopatterned Substrates. Crystal Growth and Design, 2010, 10, 2509-2514.	3.0	8
82	Electro-optic properties of GaInAsSb/GaAs quantum well for high-speed integrated optoelectronic devices. Applied Physics Letters, 2013, 102, 013120.	3.3	8
83	Abnormal photoluminescence for GaAs/Al0.2Ga0.8As quantum dot-ring hybrid nanostructure grown by droplet epitaxy. Journal of Luminescence, 2018, 195, 187-192.	3.1	8
84	Self-assembly of tensile-strained Ge quantum dots on InAlAs(111)A. Journal of Crystal Growth, 2020, 533, 125468.	1.5	8
85	Optical constants of Al0.85Ga0.15As0.56Sb0.44 and Al0.79In0.21As0.74Sb0.26. Applied Physics Letters, 2021, 119, .	3.3	8
86	Structural Engineering toward High Monochromaticity of Carbon Dots-Based Light-Emitting Diodes. Journal of Physical Chemistry Letters, 2021, 12, 12107-12113.	4.6	8
87	Formation of Self-Assembled Sidewall Nanowires on Shallow Patterned GaAs (100). IEEE Nanotechnology Magazine, 2007, 6, 70-74.	2.0	7
88	Carrier localization and <i>in-situ</i> annealing effect on quaternary Ga1âˆ’xInxAsySb1âˆ’y/GaAs quantum wells grown by Sb pre-deposition. Applied Physics Letters, 2013, 102, .	3.3	7
89	Exploring time-resolved photoluminescence for nanowires using a three-dimensional computational transient model. Nanoscale, 2018, 10, 7792-7802.	5.6	7
90	Solar-heating thermocatalytic H₂ production from formic acid by a MoS₂-graphene-nickel foam composite. Green Chemistry, 2021, 23, 7630-7634.	9.0	7

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91	Electro-optical and lasing properties of hybrid quantum dot/quantum well material system for reconfigurable photonic devices. Applied Physics Letters, 2013, 102, 053110.	3.3	6
92	Investigation of optical transitions in InAs/GaAs(Sb)/AlAsSb quantum dots using modulation spectroscopy. Applied Physics Letters, 2014, 105, 253903.	3.3	6
93	Optical characterization of type-I to type-II band alignment transition in GaAs/Al_{<i>x</i>}Ga_{1âˆ’<i>x</i>}As quantum rings grown by droplet epitaxy. Journal Physics D: Applied Physics, 2017, 50, 32LT01.	2.8	6
94	Flexibility of Ga-containing Type-II superlattice for long-wavelength infrared detection. Journal Physics D: Applied Physics, 2019, 52, 475102.	2.8	6
95	Photoluminescence characterization of wetting layer and carrier dynamics for coupled InGaAs/GaAs surface quantum dot pair structures. Optics Express, 2020, 28, 20704.	3.4	6
96	Growth and characterization of bilayer InAs/GaAs quantum dot structures. Physica Status Solidi (A) Applications and Materials Science, 2006, 203, 2403-2410.	1.8	5
97	Spectroscopic observation of developing InAs quantum dots on GaAs ringlike-nanostructured templates. Journal of Applied Physics, 2008, 104, 044310.	2.5	5
98	Coulomb effect inhibiting spontaneous emission in charged quantum dot. Applied Physics Letters, 2010, 97, .	3.3	5
99	Anisotropic electro-optic effect on InGaAs quantum dot chain modulators. Optics Letters, 2013, 38, 4262.	3.3	5
100	The continuum state in photoluminescence of type-II In0.46Al0.54As/Al0.54Ga0.46As quantum dots. Applied Physics Letters, 2016, 109, 183103.	3.3	5
101	Optical properties of bimodally distributed InAs quantum dots grown on digital AlAs0.56Sb0.44matrix for use in intermediate band solar cells. Journal of Applied Physics, 2017, 121, 214304.	2.5	5
102	Carrier dynamics of InAs quantum dots with GaAs1âˆ’xSbx barrier layers. Applied Physics Letters, 2017, 111, .	3.3	5
103	Optical Characterization of AlAsSb Digital Alloy and Random Alloy on GaSb. Crystals, 2017, 7, 313.	2.2	5
104	A three-dimensional insight into correlation between carrier lifetime and surface recombination velocity for nanowires. Nanotechnology, 2018, 29, 504003.	2.6	5
105	Broad tunability of emission wavelength by strain coupled InAs/GaAs1â€‰âˆ’â€‰xSbx quantum dot heterostructures. Journal of Applied Physics, 2019, 126, 154302.	2.5	5
106	Energyâ€Sensitive GaSb/AlAsSb Separate Absorption and Multiplication Avalanche Photodiodes for Xâ€Ray and Gammaâ€Ray Detection. Advanced Optical Materials, 2019, 7, 1900107.	7.3	5
107	Lateral carrier transfer for high density InGaAs/GaAs surface quantum dots. Journal of Luminescence, 2020, 218, 116870.	3.1	5
108	A comprehensive set of simulation tools to model and design high-performance Type-II InAs/GaSb superlattice infrared detectors. , 2019, , .		5

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109	1.52â€‚Î¼m photoluminescence emissions from InAs quantum dots grown on nanopatterned GaAs buffers. Applied Physics Letters, 2010, 97, 143111.	3.3	4
110	Interplay Effect of Excitation and Temperature on Carrier Transfer between Vertically Aligned InAs/GaAs Quantum Dot Pairs. Crystals, 2016, 6, 144.	2.2	4
111	Characterization of GaSb photodiode for gamma-ray detection. Applied Physics Express, 2016, 9, 086401.	2.4	4
112	Comparative study of photoluminescence for type-I InAs/GaAs0.89Sb0.11 and type-II InAs/GaAs0.85Sb0.15 quantum dots. Optical Materials, 2019, 98, 109479.	3.6	4
113	Plasmonic Emission of Bullseye Nanoemitters on Bi2Te3 Nanoflakes. Materials, 2020, 13, 1531.	2.9	4
114	Folded MoS2 bilayers with variable interfacial coupling revealed by Raman and Photoluminescence spectroscopy. Optical Materials, 2021, 111, 110641.	3.6	4
115	High-Speed InAs Quantum-Dot Electrooptic Phase Modulators. IEEE Photonics Technology Letters, 2011, 23, 1748-1750.	2.5	3
116	Self-catalyzed vaporâ€“liquidâ€“solid growth of InP/InAsP coreâ€“shell nanopillars. Journal of Crystal Growth, 2011, 314, 34-38.	1.5	3
117	Coexistence of type-I and type-II band alignments in In0.46Al0.54As/Ga0.46Al0.54As self-assembled quantum dots. Applied Physics Letters, 2015, 107, 183107.	3.3	3
118	Photoluminescence study of the effect of strain compensation on InAs/AlAsSb quantum dots. Journal of Crystal Growth, 2015, 425, 312-315.	1.5	3
119	Optical image processing by using a photorefractive spatial soliton waveguide. Physics Letters, Section A: General, Atomic and Solid State Physics, 2017, 381, 1207-1212.	2.1	3
120	PL of lowâ€density InAs/GaAs quantum dots with different bimodal populations. Micro and Nano Letters, 2017, 12, 599-604.	1.3	3
121	Significant suppression of surface leakage in GaSb/AlAsSb heterostructure with Al₂O₃ passivation. Japanese Journal of Applied Physics, 2019, 58, 090907.	1.5	3
122	Different optical characteristics between monolayer and bilayer WS2 due to interlayer interaction. Optik, 2022, 251, 168374.	2.9	3
123	Type-II characteristics of photoluminescence from InGaAs/GaAs surface quantum dots due to Fermi level pinning effect. Applied Surface Science, 2022, 578, 152066.	6.1	3
124	Tensile-strained self-assembly of InGaAs on InAs(111)A. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2021, 39, 062809.	1.2	3
125	Monolithic integration of a 10ÂÎ¼m cut-off wavelength InAs/GaSb type-II superlattice diode on GaAs platform. Scientific Reports, 2022, 12, .	3.3	3
126	Optical switching property of a Ce:KNSBN photorefractive volume grating controlled by the readout beam polarization. Optics Communications, 2003, 217, 111-115.	2.1	2

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127	InAs Quantum Dot Clusters Grown on GaAs Droplet Templates: Surface Morphologies and Optical Properties. Journal of Nanoscience and Nanotechnology, 2009, 9, 3320-3324.	0.9	2
128	Impact of arsenic species on self-assembly of triangular and hexagonal tensile-strained GaAs(111)A quantum dots. Semiconductor Science and Technology, 2020, 35, 105001.	2.0	2
129	Carrier Injection to In0.4Ga0.6As/GaAs Surface Quantum Dots in Coupled Hybrid Nanostructures. Crystals, 2022, 12, 319.	2.2	2
130	Photoluminescence study of exciton localization in InGaAs bulk and InGaAs/InAlAs wide quantum well on InP (001) substrate. Journal of Luminescence, 2022, 246, 118827.	3.1	2
131	Theoretical Analysis of AlAsâ‚€.â‚…â‚†Sbâ‚€.â‚„â‚„ Single Photon Avalanche Diodes With High Breakdown Probability. IEEE Journal of Quantum Electronics, 2021, 57, 1-6.	1.9	1
132	Optical and structural investigation of a 10 Î¼m InAs/GaSb type-II superlattice on GaAs. Applied Physics Letters, 2021, 118, 203102.	3.3	1
133	Abnormal temperature-dependent photoluminescence characteristics of ReS₂ nanowalls. Nanotechnology, 2021, 32, 505723.	2.6	1
134	Electron radiation effects on carrier relaxation in molecular beam and vapor deposition grown GaAs test structures. Journal of Applied Physics, 2022, 131, 075703.	2.5	1
135	The photorefractive soliton as an electro-optic modulator. , 0, , .		0
136	Improvement of holographic recording property of a Ce: KNSBN crystal by the moving grating technique. Optik, 2003, 113, 531-534.	2.9	0
137	Fidelity holographic recording in a Ce: KNSBN crystal with incoherent erasing technique. Optik, 2003, 114, 515-517.	2.9	0
138	Beam fanning effect and image storage in Ce: KNSBN crystal. Science Bulletin, 2007, 52, 1024-1028.	1.7	0
139	Type-II GaSb quantum dots grown on InAlAs/InP (001) by droplet epitaxy. Nanotechnology, 2020, 31, 315701.	2.6	0
140	Electronic excited state energy competition between donor and acceptor in oligo(phenylene vinylene) microcrystal. Optical Materials, 2020, 101, 109714.	3.6	0
141	Optimization of surface passivation for suppressing leakage current in GaSb PIN devices. Electronics Letters, 2020, 56, 1420-1423.	1.0	0